

74HC2GU04

Dual unbuffered inverter

Rev. 2 — 20 August 2014

Product data sheet

1. General description

The 74HC2GU04 is a high-speed Si-gate CMOS device.

The 74HC2GU04 provides two unbuffered inverters.

2. Features and benefits

- Wide supply voltage range from 2.0 V to 6.0 V
- Complies with JEDEC standard no. 7A
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

| Type number | Package | | | |
|-------------|-------------------|-------|--|---------|
| | Temperature range | Name | Description | Version |
| 74HC2GU04GW | –40 °C to +125 °C | SC-88 | plastic surface-mounted package; 6 leads | SOT363 |
| 74HC2GU04GV | –40 °C to +125 °C | SC-74 | plastic surface-mounted package (TSOP6); 6 leads | SOT457 |

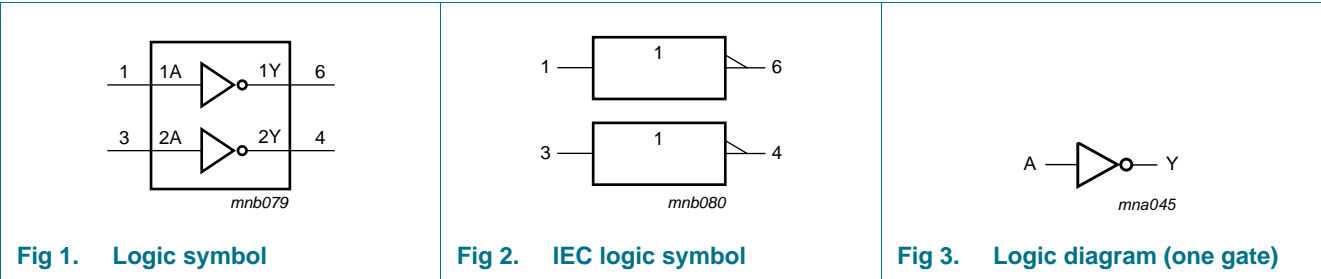
4. Marking

Table 2. Marking

| Type number | Marking code |
|-------------|--------------|
| 74HC2GU04GW | PD |
| 74HC2GU04GV | HU4 |

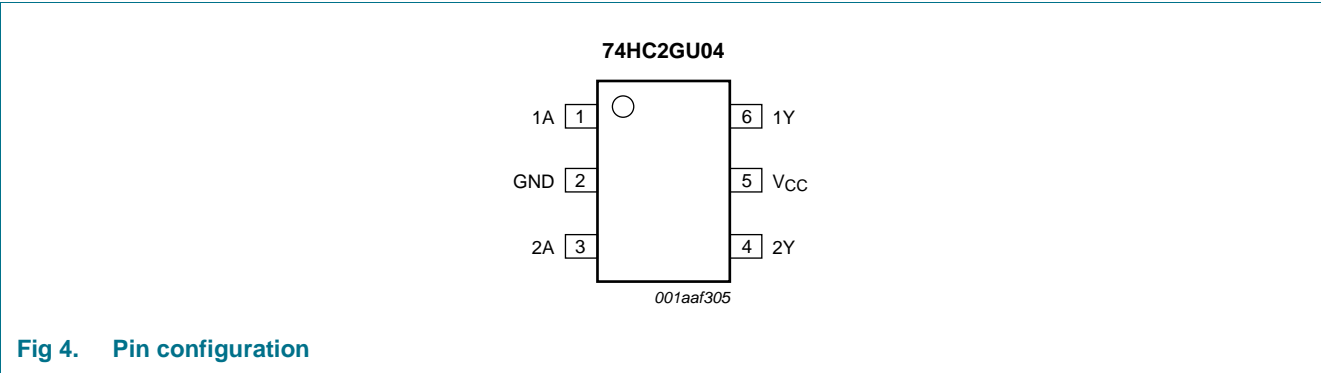


5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

| Symbol | Pin | Description |
|-----------------|-----|----------------|
| 1A | 1 | data input |
| GND | 2 | ground (0 V) |
| 2A | 3 | data input |
| 2Y | 4 | data output |
| V _{CC} | 5 | supply voltage |
| 1Y | 6 | data output |

7. Functional description

Table 4. Function table^[1]

| Input | Output |
|-------|--------|
| nA | nY |
| L | H |
| H | L |

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|-------------------------|--|------|----------|------|
| V_{CC} | supply voltage | | -0.5 | +7.0 | V |
| I_{IK} | input clamping current | $V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$ [1] | - | ± 20 | mA |
| I_{OK} | output clamping current | $V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$ [1] | - | ± 20 | mA |
| I_O | output current | $V_O = -0.5\text{ V}$ to $V_{CC} + 0.5\text{ V}$ [1] | - | ± 25 | mA |
| I_{CC} | supply current | [1] | - | +50 | mA |
| I_{GND} | ground current | [1] | - | -50 | mA |
| T_{stg} | storage temperature | | -65 | +150 | °C |
| P_{tot} | total power dissipation | [2] | - | 250 | mW |

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 and SC-74 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------|---------------------|-----------------------------------|-----|-----|----------|------|
| V_{CC} | supply voltage | | 2.0 | 5.0 | 6.0 | V |
| V_I | input voltage | | 0 | - | V_{CC} | V |
| V_O | output voltage | | 0 | - | V_{CC} | V |
| T_{amb} | ambient temperature | | -40 | +25 | +125 | °C |
| t_r | rise time | except for Schmitt trigger inputs | | | | |
| | | $V_{CC} = 2.0\text{ V}$ | - | - | 1000 | ns |
| | | $V_{CC} = 4.5\text{ V}$ | - | - | 500 | ns |
| | | $V_{CC} = 6.0\text{ V}$ | - | - | 400 | ns |
| t_f | fall time | except for Schmitt trigger inputs | | | | |
| | | $V_{CC} = 2.0\text{ V}$ | - | - | 1000 | ns |
| | | $V_{CC} = 4.5\text{ V}$ | - | - | 500 | ns |
| | | $V_{CC} = 6.0\text{ V}$ | - | - | 400 | ns |

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---------------------------|---|------|------|------|------|
| T_{amb} = 25 °C | | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 2.0 V | 1.7 | 1.1 | - | V |
| | | V _{CC} = 4.5 V | 3.6 | 2.4 | - | V |
| | | V _{CC} = 6.0 V | 4.8 | 3.1 | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 2.0 V | - | 0.9 | 0.3 | V |
| | | V _{CC} = 4.5 V | - | 2.1 | 0.9 | V |
| | | V _{CC} = 6.0 V | - | 2.9 | 1.2 | V |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = -20 µA; V _{CC} = 2.0 V | 1.9 | 2.0 | - | V |
| | | I _O = -20 µA; V _{CC} = 4.5 V | 4.4 | 4.5 | - | V |
| | | I _O = -20 µA; V _{CC} = 6.0 V | 5.9 | 6.0 | - | V |
| | | I _O = -4.0 mA; V _{CC} = 4.5 V | 4.13 | 4.32 | - | V |
| | | I _O = -5.2 mA; V _{CC} = 6.0 V | 5.63 | 5.81 | - | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = 20 µA; V _{CC} = 2.0 V | - | 0 | 0.1 | V |
| | | I _O = 20 µA; V _{CC} = 4.5 V | - | 0 | 0.1 | V |
| | | I _O = 20 µA; V _{CC} = 6.0 V | - | 0 | 0.1 | V |
| | | I _O = 4.0 mA; V _{CC} = 4.5 V | - | 0.15 | 0.26 | V |
| | | I _O = 5.2 mA; V _{CC} = 6.0 V | - | 0.16 | 0.26 | V |
| I _I | input leakage current | V _I = GND or V _{CC} ; V _{CC} = 6.0 V | - | - | ±0.1 | µA |
| I _{CC} | supply current | V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 6.0 V | - | - | 1.0 | µA |
| C _I | input capacitance | | - | 3.0 | - | pF |
| T_{amb} = -40 °C to +85 °C | | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 2.0 V | 1.7 | 1.1 | - | V |
| | | V _{CC} = 4.5 V | 3.6 | 2.4 | - | V |
| | | V _{CC} = 6.0 V | 4.8 | 3.1 | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 2.0 V | - | 0.9 | 0.3 | V |
| | | V _{CC} = 4.5 V | - | 2.1 | 0.9 | V |
| | | V _{CC} = 6.0 V | - | 2.9 | 1.2 | V |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = -20 µA; V _{CC} = 2.0 V | 1.9 | 2.0 | - | V |
| | | I _O = -20 µA; V _{CC} = 4.5 V | 4.4 | 4.5 | - | V |
| | | I _O = -20 µA; V _{CC} = 6.0 V | 5.9 | 6.0 | - | V |
| | | I _O = -4.0 mA; V _{CC} = 4.5 V | 4.13 | 4.32 | - | V |
| | | I _O = -5.2 mA; V _{CC} = 6.0 V | 5.63 | 5.81 | - | V |

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--|---------------------------|--|-----|------|------|------|
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = 20 µA; V _{CC} = 2.0 V | - | 0 | 0.1 | V |
| | | I _O = 20 µA; V _{CC} = 4.5 V | - | 0 | 0.1 | V |
| | | I _O = 20 µA; V _{CC} = 6.0 V | - | 0 | 0.1 | V |
| | | I _O = 4.0 mA; V _{CC} = 4.5 V | - | 0.15 | 0.33 | V |
| | | I _O = 5.2 mA; V _{CC} = 6.0 V | - | 0.16 | 0.33 | V |
| I _I | input leakage current | V _I = GND or V _{CC} ; V _{CC} = 6.0 V | - | - | ±1.0 | µA |
| I _{CC} | supply current | V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 6.0 V | - | - | 10.0 | µA |
| T_{amb} = -40 °C to +125 °C | | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 2.0 V | 1.7 | - | - | V |
| | | V _{CC} = 4.5 V | 3.6 | - | - | V |
| | | V _{CC} = 6.0 V | 4.8 | - | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 2.0 V | - | - | 0.3 | V |
| | | V _{CC} = 4.5 V | - | - | 0.9 | V |
| | | V _{CC} = 6.0 V | - | - | 1.2 | V |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = -20 µA; V _{CC} = 2.0 V | 1.9 | - | - | V |
| | | I _O = -20 µA; V _{CC} = 4.5 V | 4.4 | - | - | V |
| | | I _O = -20 µA; V _{CC} = 6.0 V | 5.9 | - | - | V |
| | | I _O = -4.0 mA; V _{CC} = 4.5 V | 3.7 | - | - | V |
| | | I _O = -5.2 mA; V _{CC} = 6.0 V | 5.2 | - | - | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = 20 µA; V _{CC} = 2.0 V | - | - | 0.1 | V |
| | | I _O = 20 µA; V _{CC} = 4.5 V | - | - | 0.1 | V |
| | | I _O = 20 µA; V _{CC} = 6.0 V | - | - | 0.1 | V |
| | | I _O = 4.0 mA; V _{CC} = 4.5 V | - | - | 0.4 | V |
| | | I _O = 5.2 mA; V _{CC} = 6.0 V | - | - | 0.4 | V |
| I _I | input leakage current | V _I = GND or V _{CC} ; V _{CC} = 6.0 V | - | - | ±1.0 | µA |
| I _{CC} | supply current | V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 6.0 V | - | - | 20.0 | µA |

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see [Figure 6](#).

| Symbol | Parameter | Conditions | 25 °C | | | –40 °C to +125 °C | | | Unit |
|----------|-------------------------------|--|-------|-----|-----|-------------------|-------------|--------------|------|
| | | | Min | Typ | Max | Min | Max (85 °C) | Max (125 °C) | |
| t_{pd} | propagation delay | nA to nY; see Figure 5 [1] | | | | | | | |
| | | $V_{CC} = 2.0\text{ V}; C_L = 50\text{ pF}$ | - | 13 | 60 | - | 75 | 90 | ns |
| | | $V_{CC} = 4.5\text{ V}; C_L = 50\text{ pF}$ | - | 6 | 12 | - | 15 | 18 | ns |
| | | $V_{CC} = 6.0\text{ V}; C_L = 50\text{ pF}$ | - | 5 | 10 | - | 13 | 15 | ns |
| t_t | transition time | nY; see Figure 5 [2] | | | | | | | |
| | | $V_{CC} = 2.0\text{ V}; C_L = 50\text{ pF}$ | - | 18 | 75 | - | 95 | 125 | ns |
| | | $V_{CC} = 4.5\text{ V}; C_L = 50\text{ pF}$ | - | 6 | 15 | - | 19 | 25 | ns |
| | | $V_{CC} = 6.0\text{ V}; C_L = 50\text{ pF}$ | - | 5 | 13 | - | 16 | 20 | ns |
| C_{PD} | power dissipation capacitance | $V_I = \text{GND to } V_{CC}$ [3] | - | 5 | - | - | - | - | pF |

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] t_t is the same as t_{TLH} and t_{THL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

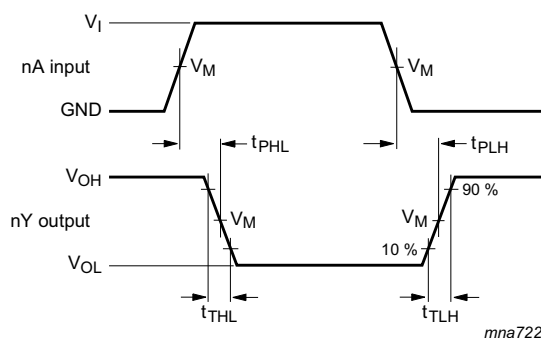
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



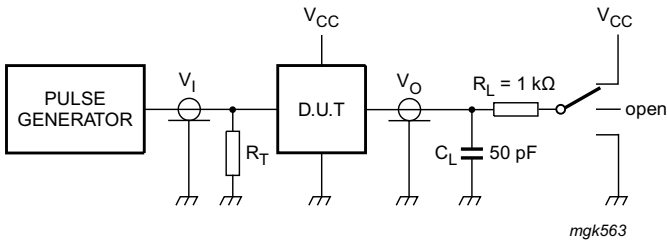
Measurement points are given in [Table 9](#).

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. The data input (nA) to output (nY) propagation delays and output transition times

Table 9. Measurement points

| Input | | | Output |
|--------------------|------------------------|---------------------------------|--------------------|
| V _M | V _I | t _r = t _f | V _M |
| 0.5V _{CC} | GND to V _{CC} | 6.0 ns | 0.5V _{CC} |



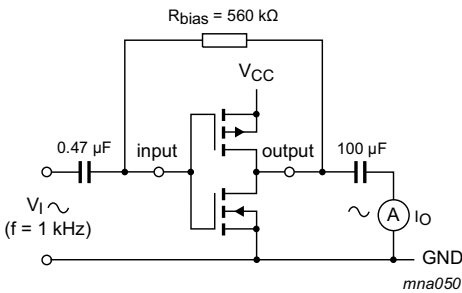
Test data is given in [Table 10](#).
Definitions test circuit:
R_L = Load resistance.
C_L = Load capacitance including jig and probe capacitance.
R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 6. Test circuit for measuring switching times

Table 10. Test data

| Input | | Test |
|------------------------|---------------------------------|-------------------------------------|
| V _I | t _r , t _f | t _{PHL} , t _{PLH} |
| GND to V _{CC} | 6 ns | open |

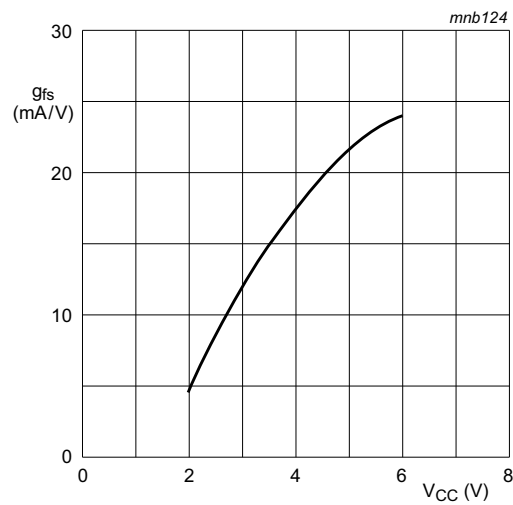
13. Additional characteristics



$$g_{fs} = \frac{\Delta I_o}{\Delta V_i}$$

V_O is constant.

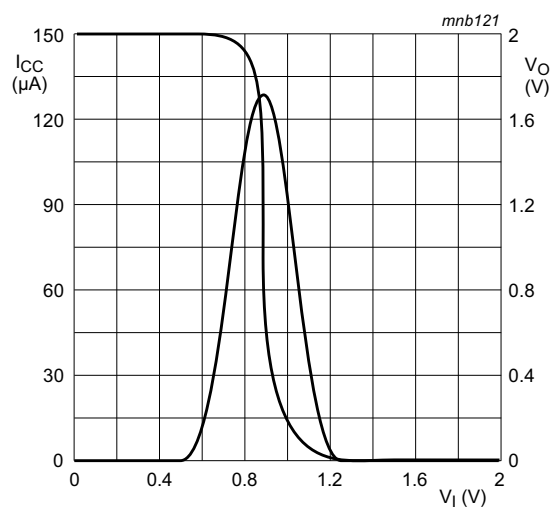
Fig 7. Test setup for measuring forward transconductance



$T_{amb} = 25\text{ }^{\circ}\text{C}$.

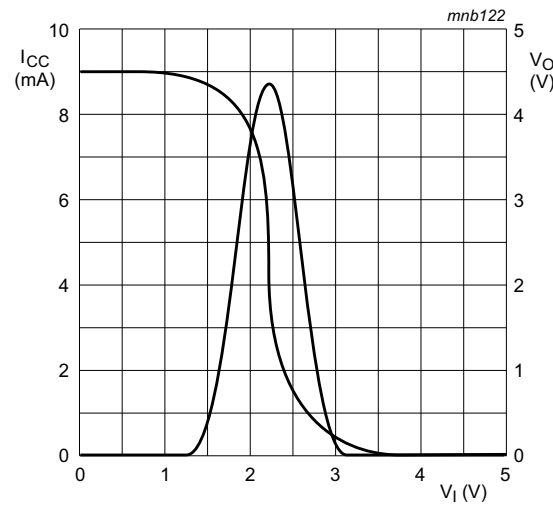
Fig 8. Typical forward transconductance as a function of supply voltage

14. Typical transfer characteristics



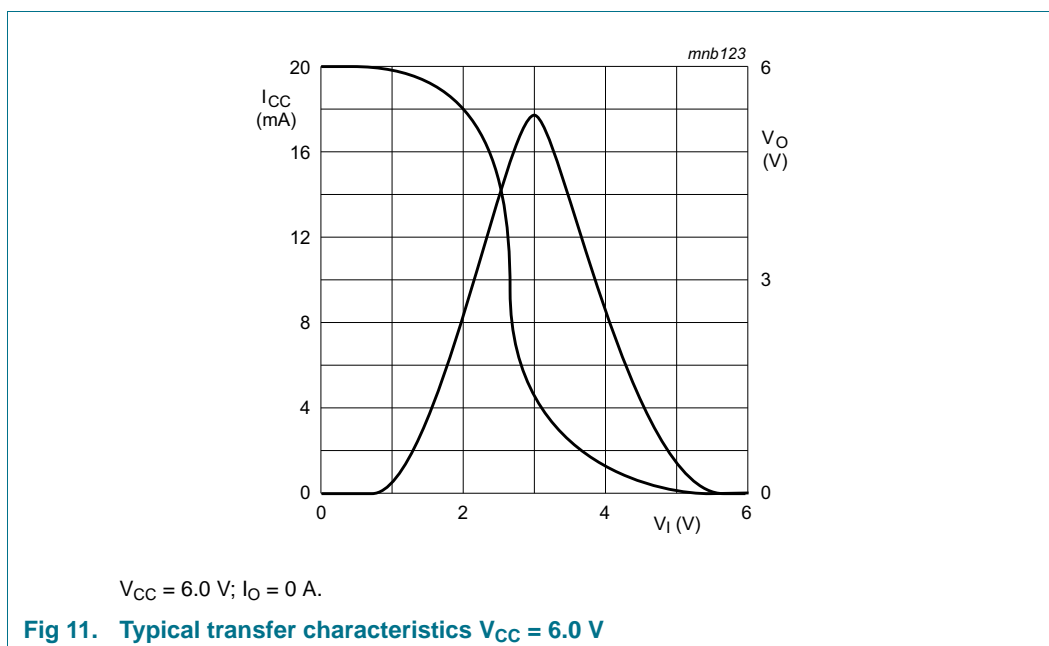
$V_{CC} = 2.0\text{ V}$; $I_O = 0\text{ A}$.

Fig 9. Typical transfer characteristics $V_{CC} = 2.0\text{ V}$



$V_{CC} = 4.5\text{ V}$; $I_O = 0\text{ A}$.

Fig 10. Typical transfer characteristics $V_{CC} = 4.5\text{ V}$

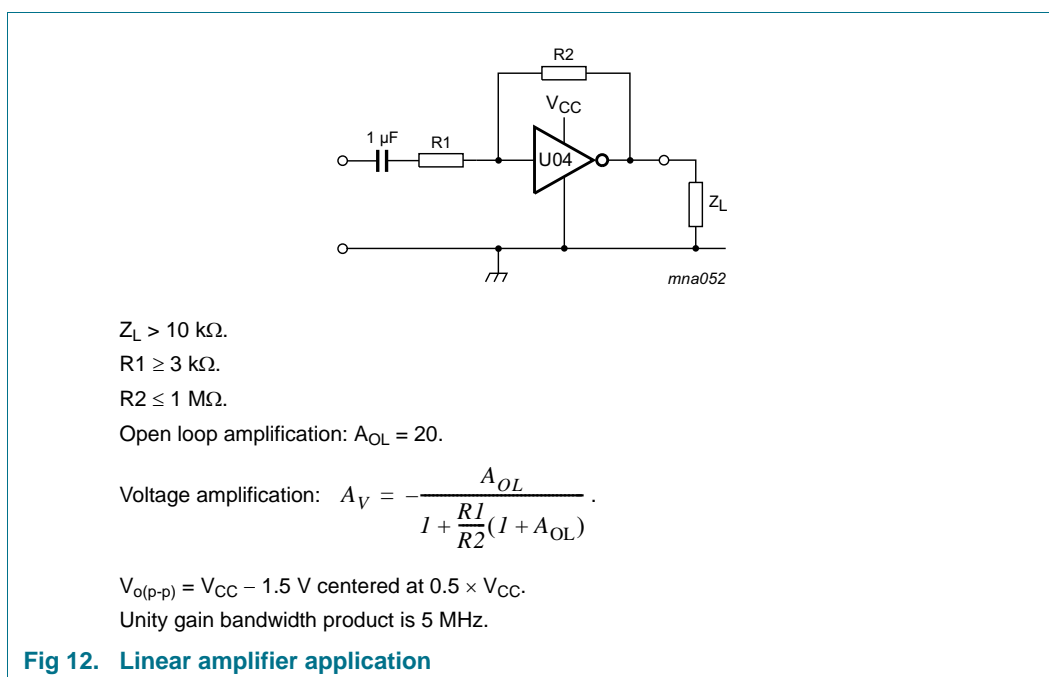


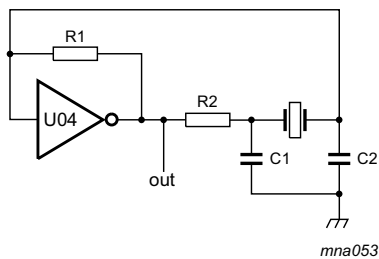
15. Application information

Some applications for the 74HC2GU04 are:

- Linear amplifier (see [Figure 12](#))
- Crystal oscillator (see [Figure 13](#))

Remark: All values given are typical values unless otherwise specified.





See [Table 11](#) and [Table 12](#).
C1 = 47 pF.
C2 = 22 pF.
R1 = 1 MΩ to 10 MΩ.
R2 optimum value depends on the frequency and required stability against changes in V_{CC} or average minimum I_{CC} (I_{CC} = 2 mA at V_{CC} = 3.0 V and f = 1 MHz).

Fig 13. Crystal oscillator application

Table 11. External components for resonator (f < 1 MHz)

| Frequency | R1 | R2 | C1 | C2 |
|----------------------|--------|--------|-------|-------|
| 10 kHz to 15.9 kHz | 2.2 MΩ | 220 kΩ | 56 pF | 20 pF |
| 16 kHz to 24.9 kHz | 2.2 MΩ | 220 kΩ | 56 pF | 10 pF |
| 25 kHz to 54.9 kHz | 2.2 MΩ | 100 kΩ | 56 pF | 10 pF |
| 55 kHz to 129.9 kHz | 2.2 MΩ | 100 kΩ | 47 pF | 5 pF |
| 130 kHz to 199.9 kHz | 2.2 MΩ | 47 kΩ | 47 pF | 5 pF |
| 200 kHz to 349.9 kHz | 2.2 MΩ | 47 kΩ | 47 pF | 5 pF |
| 350 kHz to 600 kHz | 2.2 MΩ | 47 kΩ | 47 pF | 5 pF |

Table 12. Optimum value for R2

| Frequency | R2 | Optimum |
|-----------|------------------------------------|--|
| 3 kHz | 2.0 kΩ | for minimum required I _{CC} |
| | 8.0 kΩ | for minimum influence due to change in V _{CC} |
| 6 kHz | 1.0 kΩ | or minimum required I _{CC} |
| | 4.7 kΩ | or minimum influence by V _{CC} |
| 10 kHz | 0.5 kΩ | or minimum required I _{CC} |
| | 2.0 kΩ | or minimum influence by V _{CC} |
| 14 kHz | 0.5 kΩ | or minimum required I _{CC} |
| | 2.0 kΩ | or minimum influence by V _{CC} |
| > 14 kHz | replace R2 by C3 = 35 pF (typical) | |

16. Package outline

Plastic surface-mounted package; 6 leads

SOT363

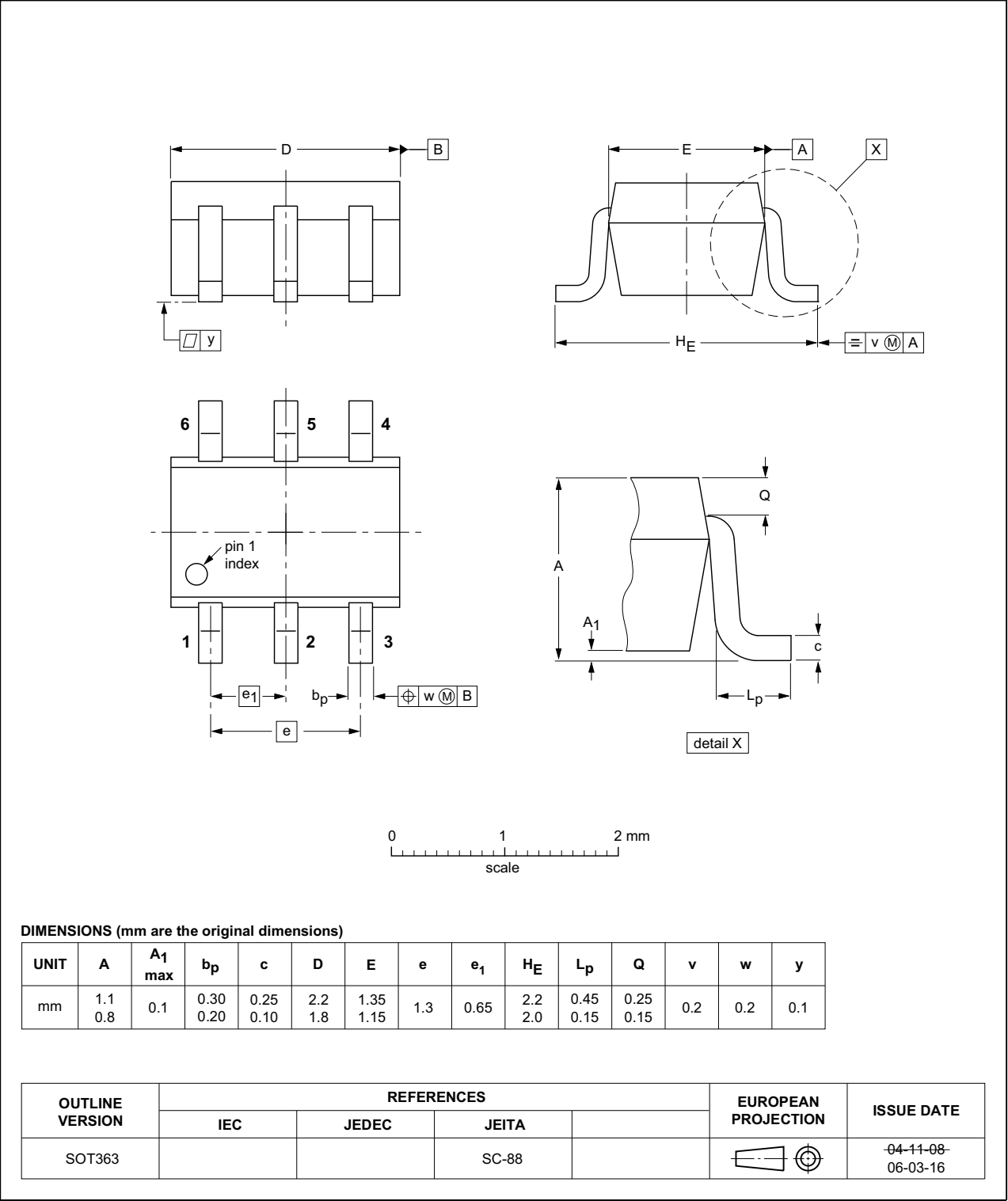


Fig 14. Package outline SOT363 (SC-88)

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

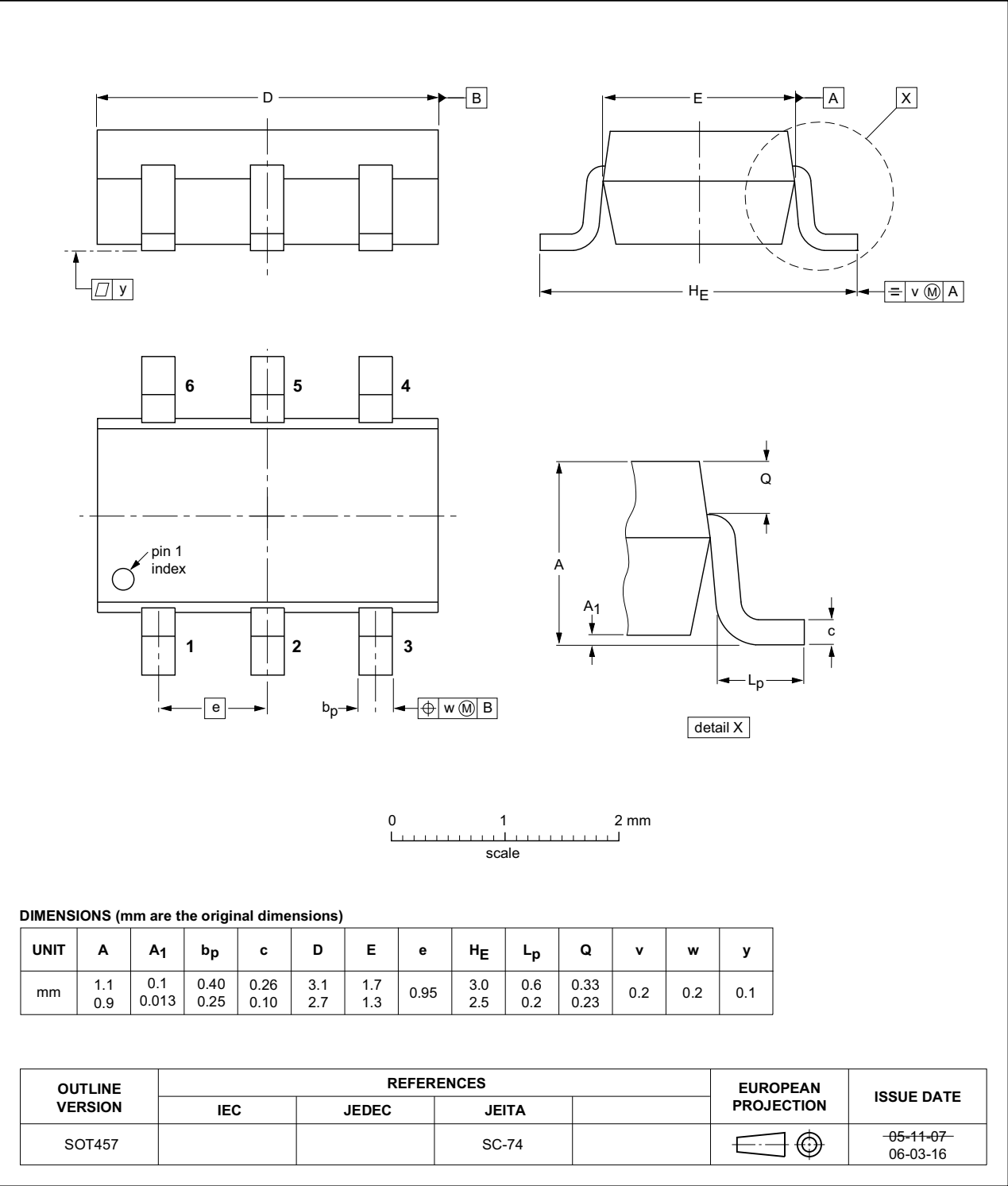


Fig 15. Package outline SOT457 (SC-74)

17. Abbreviations

Table 13. Abbreviations

| Acronym | Description |
|---------|---|
| CMOS | Complementary Metal-Oxide Semiconductor |
| DUT | Device Under Test |
| ESD | ElectroStatic Discharge |
| HBM | Human Body Model |
| MM | Machine Model |

18. Revision history

Table 14. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--|--------------------|---------------|---------------|
| 74HC2GU04 v.2 | 20140820 | Product data sheet | - | 74HC2GU04 v.1 |
| Modifications: | <ul style="list-style-type: none">The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.Legal texts have been adapted to the new company name where appropriate. | | | |
| 74HC2GU04 v.1 | 20061006 | Product data sheet | - | - |

19. Legal information

19.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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